

30 A, 1200 V, Hyperfast Diode

The RHRP30120 is a hyperfast diode with soft recovery characteristics. It has the half recovery time of ultrafast diodes and is silicon nitride passivated ionimplanted epitaxial planar construction. These devices are intended to be used as freewheeling/ clamping diodes and diodes in a variety of switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

Ordering Information

PART NUMBER	PACKAGE	BRAND
RHRP30120	TO-220AC	RHR30120

NOTE: When ordering, use the entire part number.

Features

- Hyperfast Recovery $t_{rr} = 85 \text{ ns}$ (@ $I_F = 30 \text{ A}$)
- Max Forward Voltage, $V_F = 3.2 \text{ V}$ (@ $T_C = 25^\circ\text{C}$)
- 1200 V Reverse Voltage and High Reliability
- Avalanche Energy Rated
- RoHS Compliant

Applications

- Switching Power Supplies
- Power Switching Circuits
- General Purpose

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

	RHRP30120	UNIT
Peak Repetitive Reverse Voltage V_{RRM}	1200	V
Working Peak Reverse Voltage V_{RWM}	1200	V
DC Blocking Voltage V_R	1200	V
Average Rectified Forward Current $I_{F(AV)}$ ($T_C = 78^\circ\text{C}$)	30	A
Repetitive Peak Surge Current I_{FRM} (Square Wave, 20 kHz)	60	A
Nonrepetitive Peak Surge Current I_{FSM} (Halfwave, 1 Phase, 60 Hz)	300	A
Maximum Power Dissipation P_D	125	W
Avalanche Energy (See Figures 7 and 8) E_{AVL}	30	mJ
Operating and Storage Temperature T_{STG}, T_J	-65 to 175	$^\circ\text{C}$

Electrical Specifications $T_C = 25^{\circ}\text{C}$, Unless Otherwise Specified

SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
V_F	$I_F = 30\text{ A}$	-	-	3.2	V
	$I_F = 3.0\text{ A}, T_C = 150^{\circ}\text{C}$	-	-	2.6	V
I_R	$V_R = 1200\text{ V}$	-	-	250	μA
	$V_R = 1200\text{ V}, T_C = 150^{\circ}\text{C}$	-	-	1	mA
t_{rr}	$I_F = 1\text{ A}, dI_F/dt = 100\text{ A}/\mu\text{s}$	-	-	65	ns
	$I_F = 3.0\text{ A}, dI_F/dt = 100\text{ A}/\mu\text{s}$	-	-	85	ns
t_a	$I_F = 3.0\text{ A}, dI_F/dt = 100\text{ A}/\mu\text{s}$	-	48	-	ns
t_b	$I_F = 3.0\text{ A}, dI_F/dt = 100\text{ A}/\mu\text{s}$	-	22	-	ns
$R_{\theta JC}$		-	-	1.2	$^{\circ}\text{C}/\text{W}$

DEFINITIONS

- V_F = Instantaneous forward voltage (pw = 300 μs , D = 2%).
- I_R = Instantaneous reverse current.
- T_{rr} = Reverse recovery time (See Figure 6), summation of $t_a + t_b$.
- t_a = Time to reach peak reverse current (See Figure 6).
- t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 6).
- $R_{\theta JC}$ = Thermal resistance junction to case.
- pw = pulse width.
- D = duty cycle.

Typical Performance Curves

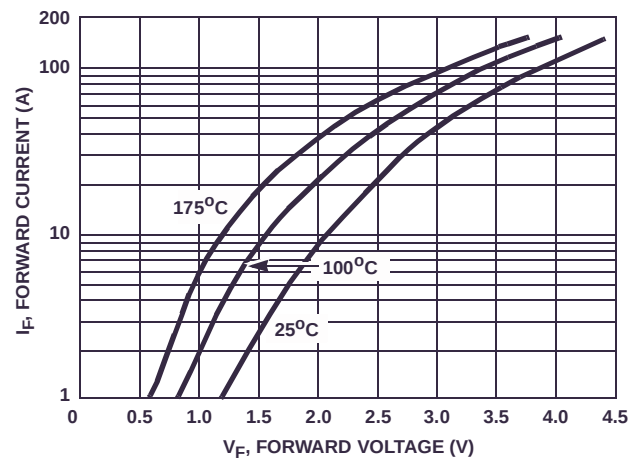


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

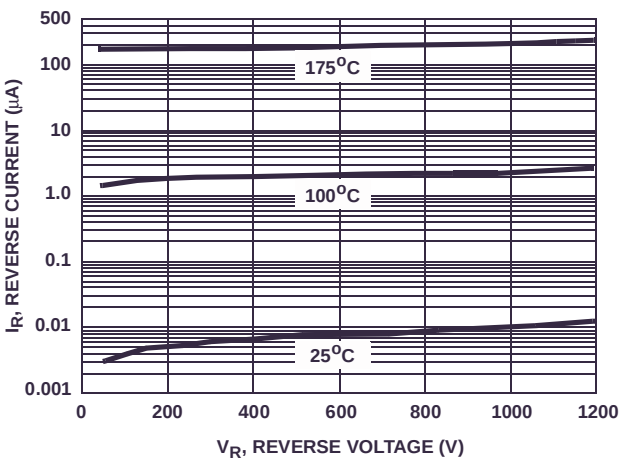


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

Typical Performance Curves (Continued)

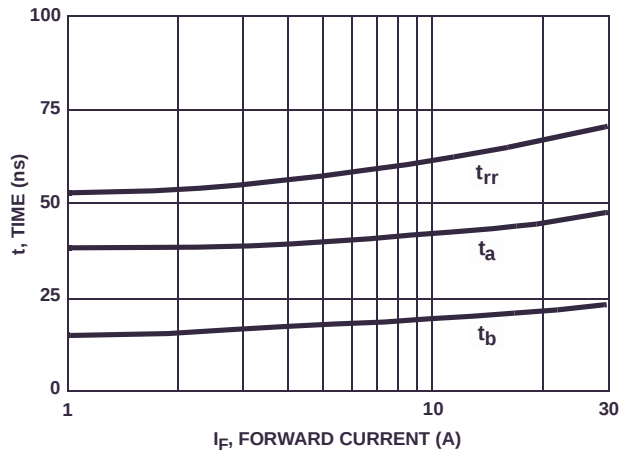


FIGURE 3. t_{rr} , t_a AND t_b CURVES vs FORWARD CURRENT

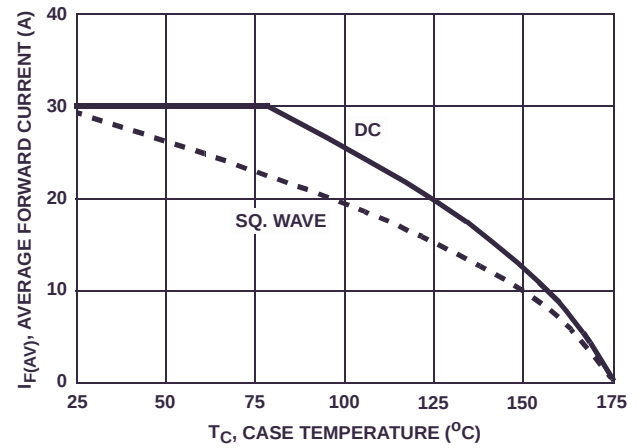


FIGURE 4. CURRENT DERATING CURVE

Test Circuits and Waveforms

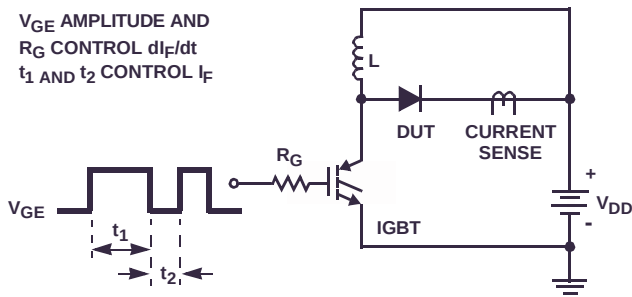


FIGURE 5. t_{rr} TEST CIRCUIT

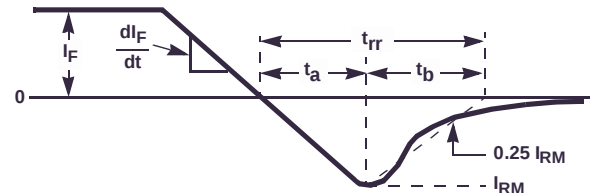


FIGURE 6. t_{rr} WAVEFORMS AND DEFINITIONS

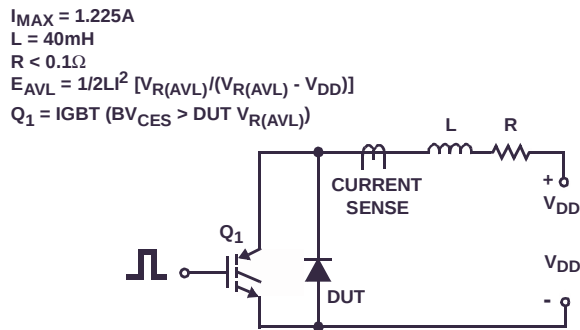


FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT

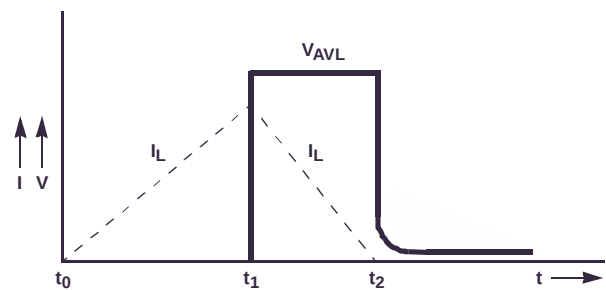


FIGURE 8. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS